

## M615x Series

5.0 x 7.0 mm, 3.0, 3.3 & 5.0 V, HCMOS or Clipped Sine Wave,  
Precision TCXO/TCVCXO

### Product Features

#### Features

- Stratum 3 Performance with 0.34 ppm (pk-pk) Holdover Stability Over Industrial Temperature Range (-40 °C to +85 °C)
- 3.0 V, 3.3 V and 5.0 V Options
- Low Phase Noise and Excellent G-Sens Performance (1.5 ppb/g)
- Tristate Function Available
- Available in Clipped Sine Wave or HCMOS



#### Applications

- Synchronous Ethernet Slave Clocks ITU-T G.8262 EEC Options 1 & 2
- Compliant to Stratum 3 GR-1244-Core & GR-253-Core
- SONET/SDH Network Timing
- Wireless Communications

### Product Description

MtronPTI's M615x Series TCXO and TCVCXO provide network and wireless engineers with low voltage, surface mount products with extremely tight stability over temperature and time. MtronPTI's unique approach to crystal compensation enables these devices to achieve full Stratum 3 compliance, including holdover stability over the industrial temperature range (-40 °C to +85 °C). Specially processed crystals enable the M615x to achieve consistent long-term stability and minimal frequency shift after reflow. This processing also achieves excellent g-sensitivity (1.5 ppb/g). The low phase noise (-155 dBc/Hz at 100 kHz offset) makes the M615x ideal for the design engineer working on all types of systems as the reference timing source.

### Product Ordering Information

#### Ordering Information

	<b>M6151</b>	<b>2</b>	<b>S</b>	<b>T</b>	<b>S</b>	<b>N</b>	<b>00.0000 MHz</b>
<b>Product Series</b>							
M6150 = 5.0 V							
M6151 = 3.3 V							
M6152 = 3.0 V							
<b>Temperature Range</b>							
1: 0 °C to +70 °C      8: 0 °C to +50 °C							
2: -40 °C to +85 °C      F: -30 °C to +75 °C							
6: -20 °C to +70 °C							
<b>Stability</b>							
S: ±4.6 ppm w/Holdover							
<b>Output Type</b>							
T: Voltage Controlled With Tristate							
F: No Voltage Control With Tristate							
<b>Output Waveform</b>							
C: HCMOS							
S: Clipped Sine Wave							
<b>Package/Lead Configurations</b>							
N: Leadless Ceramic (10 pads)							
<b>Frequency (customer specified)</b>							

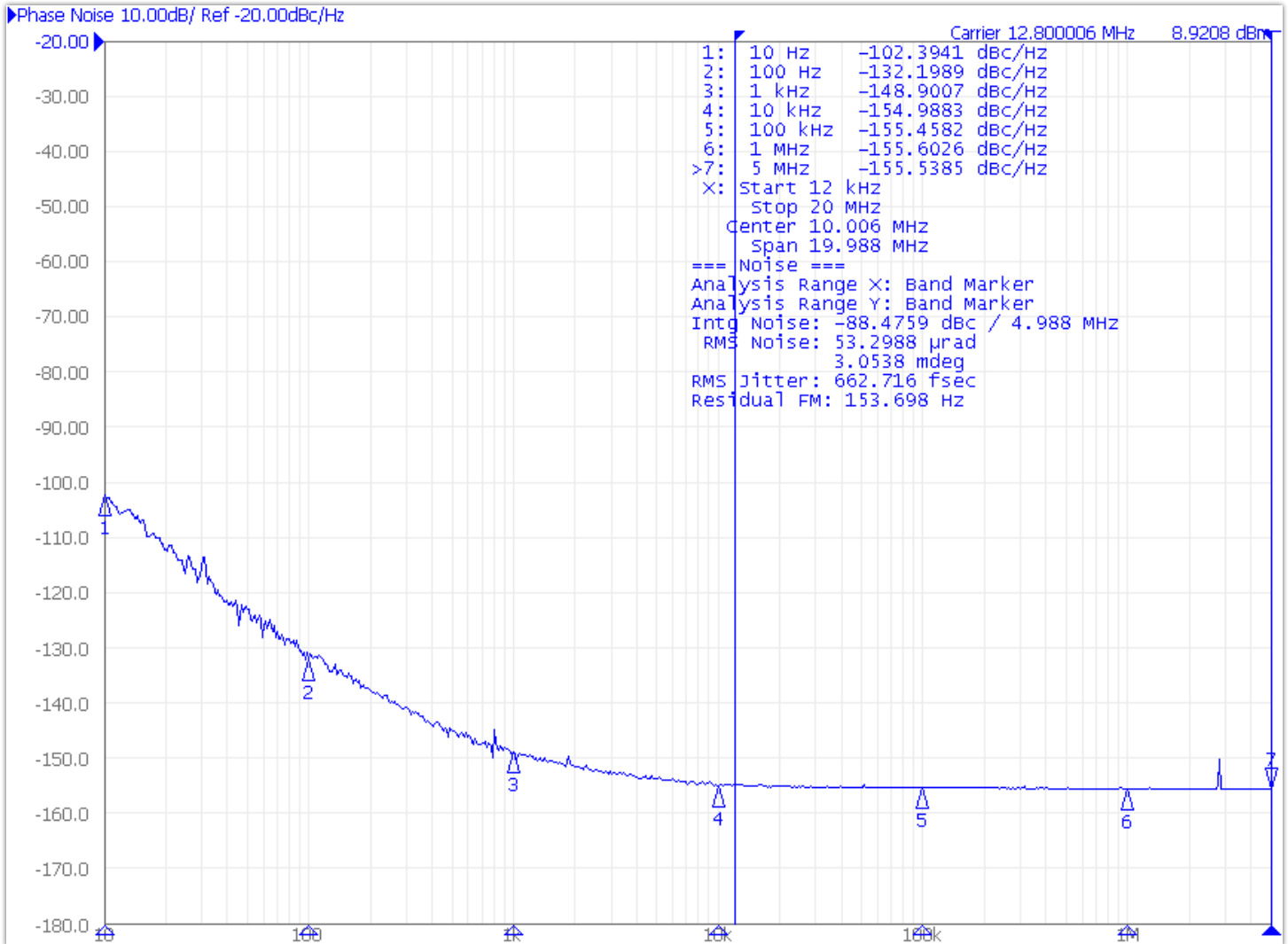
M615xSxxx - Custom datasheets.

## Performance Characteristics

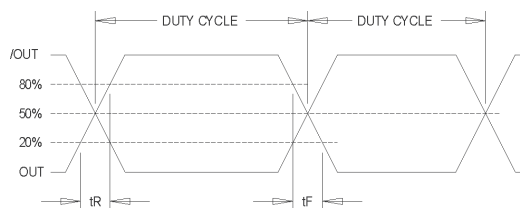
Parameter	Symbol	Min.	Typ.	Max.	Units	Conditions/Notes
Frequency Range	$F_O$	8		38.88	MHz	Contact factory above 38.88 MHz.
Initial Accuracy	$F_I$	-1.0		+1.0	ppm	@ +25 °C at time of shipment.
Operating Temperature	$T_A$	(See Ordering Information)			°C	
Storage Temperature	$T_{STG}$	-55		+125	°C	
<b>Frequency Stabilities</b>						
Stability vs Temperature	$\Delta F_T/F$			0.3	ppm	$T_A = -40$ °C to +85 °C (includes Hysteresis) Ref GR1244CORE
Stability vs Drift				40	ppb	After 24 hours at constant temperature.
Free-Run Accuracy		-4.6		+4.6	ppm	Includes initial calibration @ +25 °C, deviation over temperature, supply voltage and load variations, reflow, hysteresis, and 20 year aging.
Stability vs Supply Voltage	$\Delta F_{VDD}/F$		±0.02	±0.1	ppm	±5 % change in voltage.
Stability vs Load	$\Delta F_{LOAD}/F$		±0.02	±0.1	ppm	±5 % change in load.
<b>Supply Voltage &amp; Current</b>						
Supply Voltage ( $V_{DD}$ ) Tolerance		-5.0		+5.0	%	(See Ordering Information)
Supply Current ( $I_D$ ) (Reference to $V_{DD} = 3.3$ V)			2.0 3.0 4.2 1.3 1.7 2.3	3.0 4.0 5.2 2.0 2.7 3.5	mA mA mA mA mA mA	HCMOS output at 13 MHz HCMOS output at 26 MHz HCMOS output at 38.88 MHz Clipped Sine Wave output at 13 MHz Clipped Sine Wave output at 26 MHz Clipped Sine Wave output at 38.88 MHz
<b>RF Output</b>						
Output Logic Levels (HCMOS)	$V_{OL}$ $V_{OH}$	80		20	% $V_{DD}$ % $V_{DD}$	$I_{OH}/I_{OL} = \pm 4$ mA, $V_{DD} = +3.0$ V $I_{OH}/I_{OL} = \pm 4$ mA, $V_{DD} = +3.0$ V
Output Level (Clipped Sine Wave)		1.0 0.8			$V_{pk-pk}$ $V_{pk-pk}$	$F_O < 40$ MHz $F_O > 40$ MHz
Symmetry (Duty Cycle)	$t_{DC}$	40	50	60	%	Ref. to $\frac{1}{2} V_S$ . HCMOS Only
Rise/Fall Time	$t_R/t_F$			6.5	ns	Ref. 10 % to 90 %. HCMOS only
Output Load		15 pF 10 k $\Omega$    10 pF				HCMOS Output Clipped Sine Wave Output
Frequency Adjustment		±9.2			ppm	Over Control Voltage Range
Control Voltage Range		0.3 0.3 0.5		2.7 3.0 4.5	V V V	For $V_{DD} = 3.0$ V For $V_{DD} = 3.3$ V For $V_{DD} = 5.0$ V
Input Leakage Current		-50		+50	µA	
Input Resistance		100			k $\Omega$	
Linearity				5	%	
Modulation Bandwidth		2 kHz				
<b>Other Parameters</b>						
Tristate Function		70		30	% $V_{DD}$ % $V_{DD}$	Output enabled. Logic "1" or "Open" Output disabled. Logic "0" or "GND"
Tristate Leakage Current		-100		+100	µA	
Phase Noise (Typical 12.8 MHz HCMOS @ 3.3 V)			-102 -132 -148 -154 -155		dBc/Hz dBc/Hz dBc/Hz dBc/Hz dBc/Hz	@ 10 Hz Offset @ 100 Hz Offset @ 1 kHz Offset @ 10 kHz Offset @ 100 kHz Offset
<b>Environmental</b>						
Shock	MIL-STD-202, Method 213, Condition C (100 g)					
Vibration	MIL-STD-202, Methods 201 & 204 (10 g from 10 Hz to 2000 Hz)					
Solderability	EIAJ-STD-002					
Package	5.0 mm x 7.0 mm, SMT and DIP (RoHS Compliant)					
Max Soldering Conditions	See solder profile					

**Phase Noise Plot**

**M615x 12.8 MHz Phase Noise**

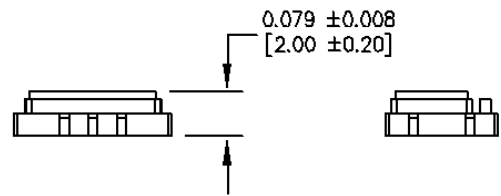
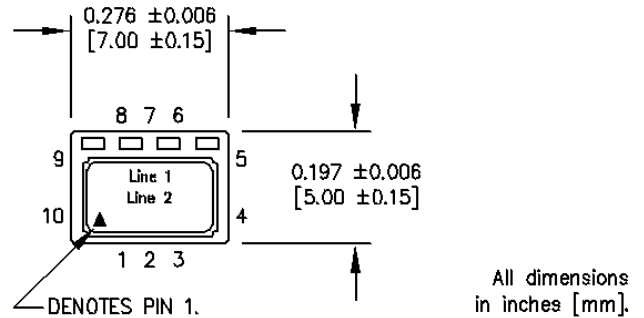


**Output Waveform (HCMOS Output)**

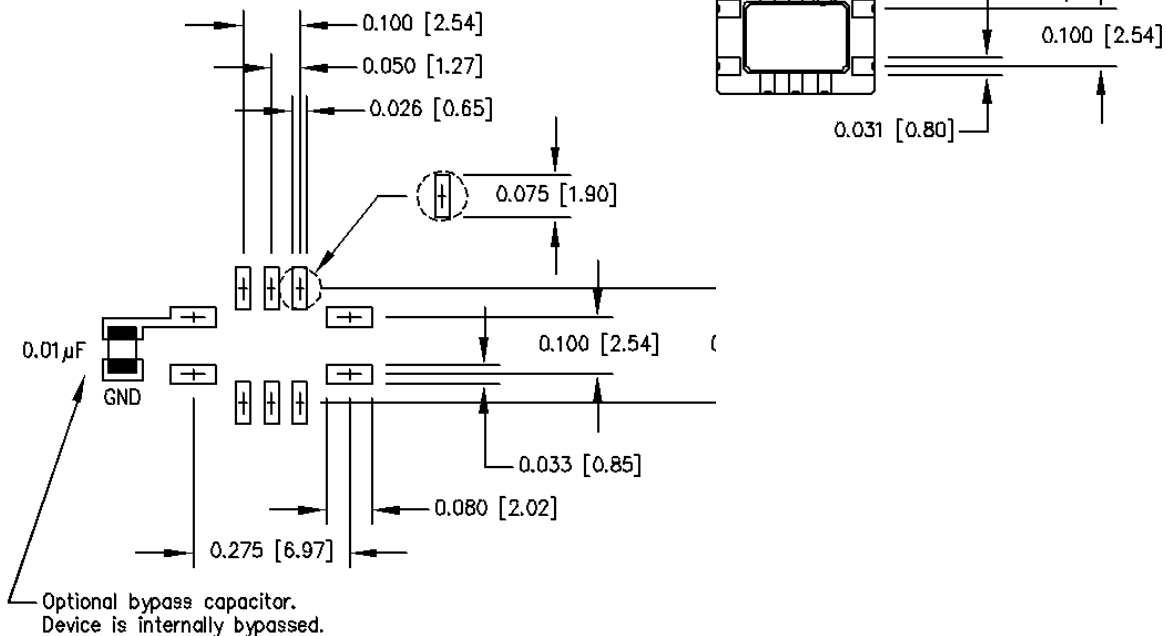


## Product Dimension & Pinout Information

Pin Connections	
Function	Pad
N/C - Do Not Connect	1
N/C - Do Not Connect	2
N/C - Do Not Connect	3
Ground	4
Output	5
N/C - Do Not Connect	6
N/C - Do Not Connect	7
Tristate	8
Supply Voltage ( $V_{DD}$ )	9
Control Voltage	10



### SUGGESTED SOLDER PAD LAYOUT



**Handling Information**

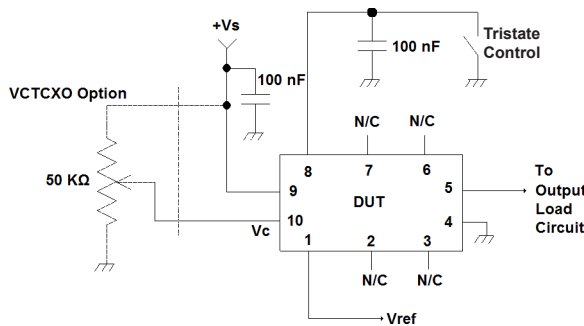
Although protection circuitry has been designed into the M615x oscillator, proper precautions should be taken to avoid exposure to electrostatic discharge (ESD) during handling and mounting. MtronPTI utilizes a human-body model (HBM) and a charged-device model (CDM) for ESD-susceptibility testing and protection design evaluation. ESD voltage thresholds are dependent on the circuit parameters used to define the mode. Although no industry-wide standard has been adopted for the CDM, a standard HBM (resistance = 1500 Ω, capacitance = 100 pF) is widely used and therefore can be used for comparison purposes. The HBM ESD threshold presented here was obtained using these circuit parameters.

Model	ESD Threshold, Minimum	Unit
Human Body	1500*	V
Charged Device	1500*	V

\* MIL-STD-883D, Method 3015, Class 1



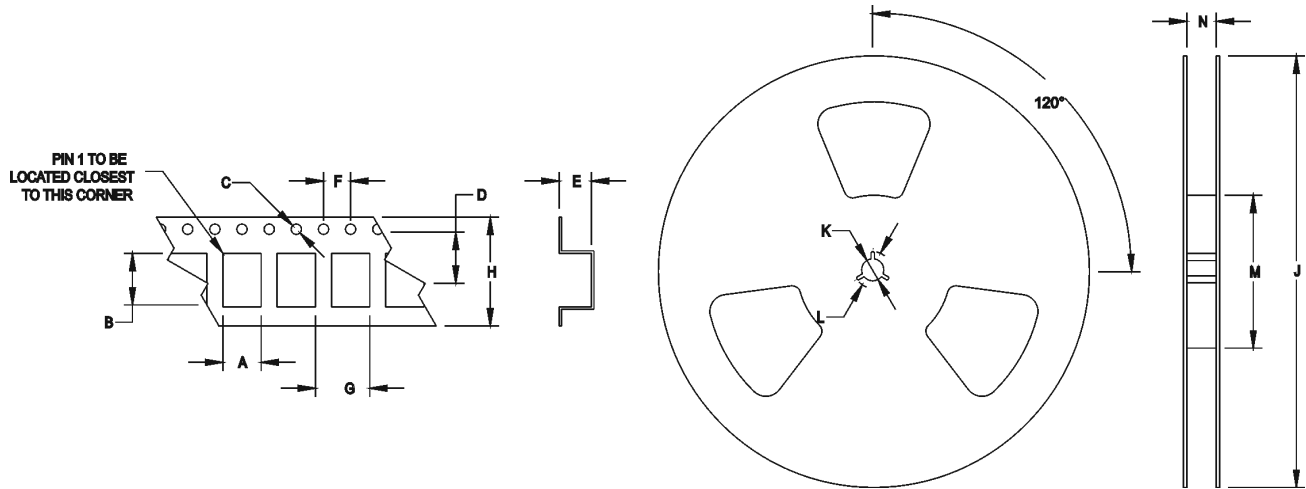
**Typical Test Circuits**



Test Circuit - N Package  
With Tristate

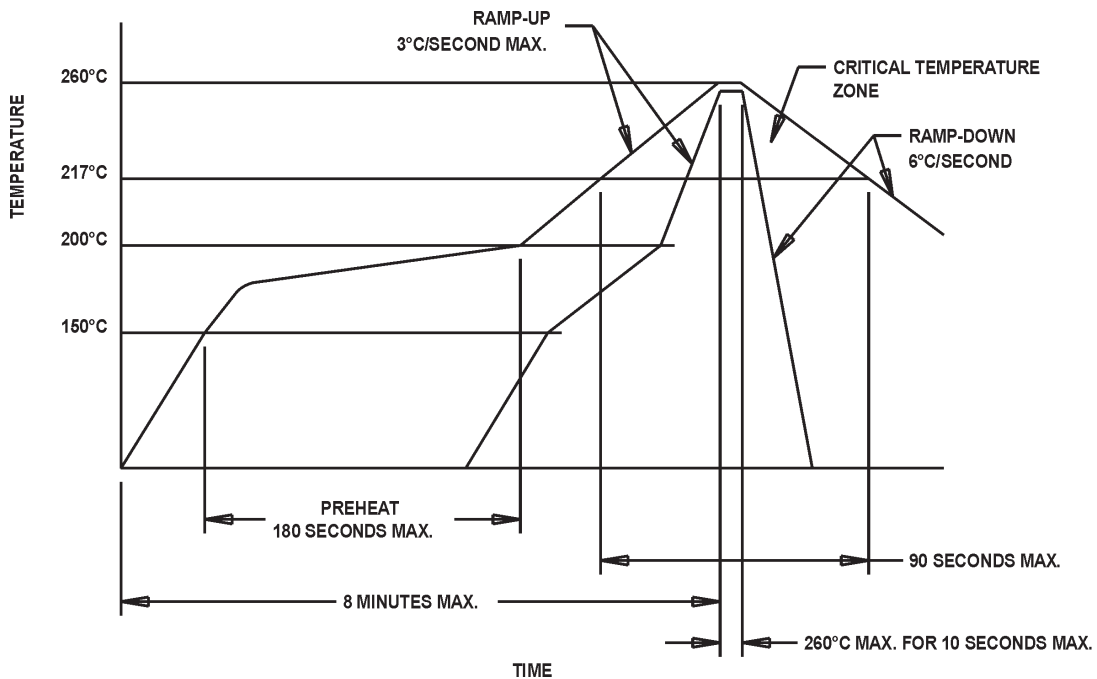
**Tape & Reel Specifications**

(all measurements are in mm)	A	B	C	D	E	F	G	H	J	K	L	M	N
M615x	5.40	7.40	1.55	7.50	2.60	2.00	4.00	16.00	330	13.00	20.20	100	16.40



Standard Tape and Reel: 1000 parts per reel

**Maximum Soldering Conditions**



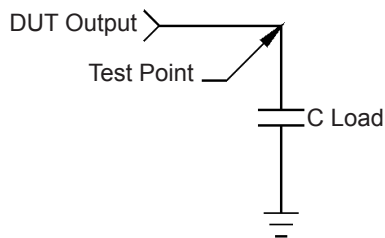
*Note: Exceeding these limits may damage the device.*

**Quality Parameters**

Environmental Specifications/Qualification Testing Performed		
Test	Test Method	Test Condition
Electrical Characteristics	Internal Specification	Per Specification
Frequency vs. Temperature	Internal Specification	Per Specification
Mechanical Shock	MIL-STD-202, Method 213, C	100 g's
Vibration	MIL-STD-202, Method 201-204	10 g's from 10-2000 Hz
Thermal Cycle	MIL-STD-883, Method 1010, B	-55 Deg. C to +125 Deg. C, 15 minute Dwell, 10 cycles
Aging	Internal Specification	168 Hours at 105 Degrees C
Gross Leak	MIL-STD-202, Method 112	30 Second Immersion
Fine Leak	MIL-STD-202, Method 112	Must meet 1x10 <sup>-8</sup>
Solderability	MIL-STD-883, Method 2003	8 Hour Steam Age – Must Exhibit 95% coverage
Resistance to Solvents	MIL-STD-883, Method 2015	Three 1 minute soaks
Physical Dimensions	MIL-STD-883, Method 2016	Per Specification
Internal Visual	Internal Specification	Per Internal Specification

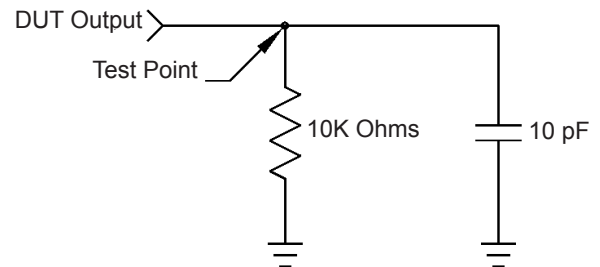
**Load Circuit**

Load Circuit #2 - HCMOS Output



Note: C Load includes probe and fixturing.

Load Circuit #7 - Clipped Sine Wave Output



For custom products or additional specifications contact our sales team at  
**800.762.8800 (toll free) or 605.665.9321**

For more information on this product visit the MtronPTI website at  
**[www.mtronpti.com](http://www.mtronpti.com)**